

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C
-60V	48mΩ @ V <sub>GS</sub> = -10V	-26A
	60mΩ @ V <sub>GS</sub> = -4.5V	-23A

## Description

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

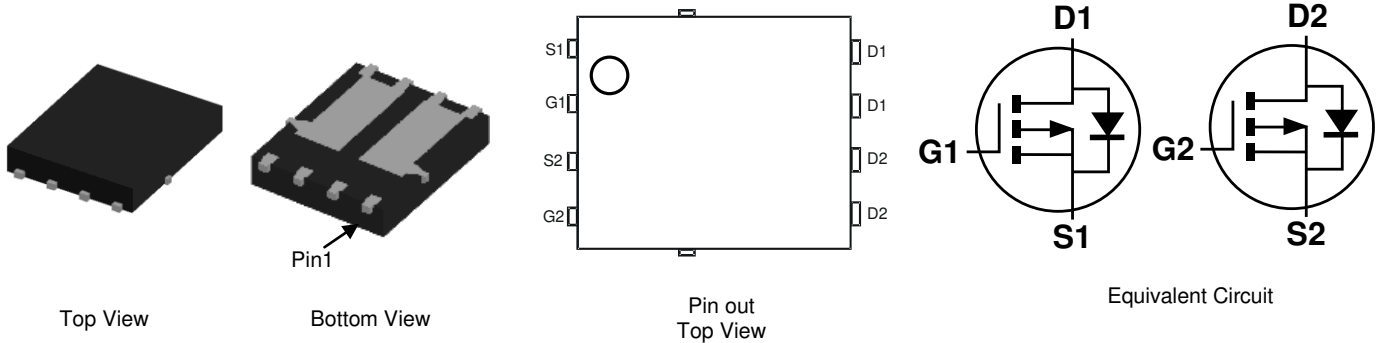
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

## Features

- Rated to +175°C – ideal for high ambient temperature environments
- 100% Unclamped Inductive Switching – ensures more reliable and robust end application
- Low R<sub>DS(ON)</sub> – minimises power losses
- Low Q<sub>g</sub> – minimises switching losses
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMPH6050SPDQ](#))**

## Mechanical Data

- Case: PowerDI5060-8 (Type C)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.097 grams (Approximate)

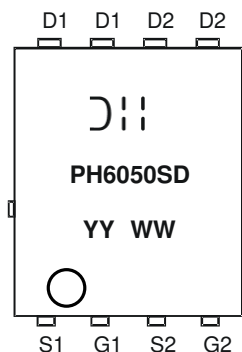


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH6050SPD-13	PowerDI5060-8 (Type C)	2500 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



☺||| = Manufacturer's Marking  
 PH6050SD = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 16 = 2016)  
 WW = Week (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	-60	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	I <sub>D</sub>	T <sub>A</sub> = +25°C T <sub>A</sub> = +100°C	-6.3 -4.4	A
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V		T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C	-26 -18	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-40	A	
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	-2.0	A	
Avalanche Current (Note 8) L = 0.1mH	I <sub>AS</sub>	-21	A	
Avalanche Energy (Note 8) L = 0.1mH	E <sub>AS</sub>	30	mJ	

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.5	W	
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	Steady state	100	°C/W
		t < 10s	53	
Total Power Dissipation (Note 6)	P <sub>D</sub>	2.8	W	
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	Steady state	52	°C/W
		t < 10s	27	
Thermal Resistance, Junction to Case (Note 7)	R <sub>θJC</sub>	2.9		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C	

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 9)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 9)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	—	-3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	36	48	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -5A V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4A
			44	60		
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 10)</b>						
Input Capacitance	C <sub>iss</sub>	—	1525	—	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	90	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	70	—	pF	
Gate Resistance	R <sub>g</sub>	—	16	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	14.5	—	nC	
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	30.6	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	4.9	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	5.2	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	5.3	—	ns	
Turn-On Rise Time	t <sub>R</sub>	—	15.4	—	ns	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -30V, R <sub>G</sub> = 3Ω, I <sub>D</sub> = -5A
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	79.2	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	45.3	—	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	15.2	—	ns	I <sub>F</sub> = -5A, di/dt = -100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	9.3	—	nC	I <sub>F</sub> = -5A, di/dt = -100A/µs

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

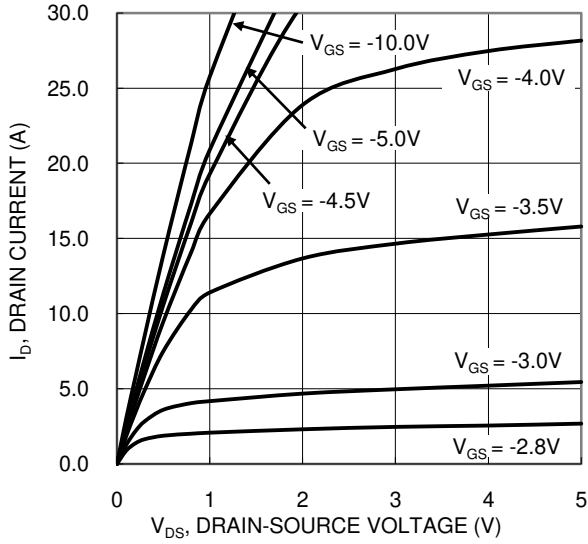


Figure 1. Typical Output Characteristic

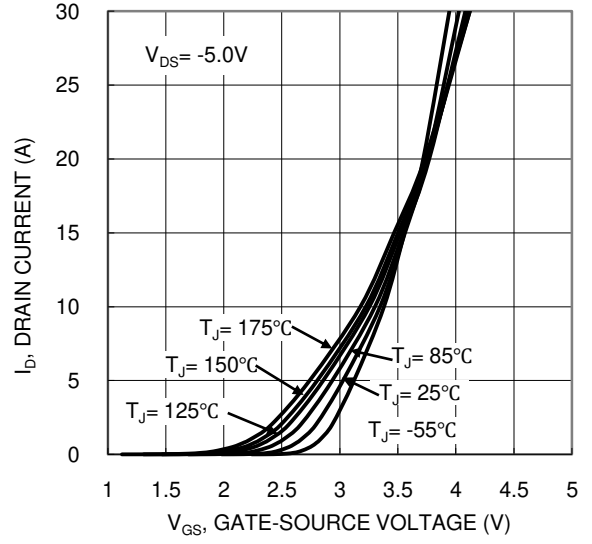


Figure 2. Typical Transfer Characteristic

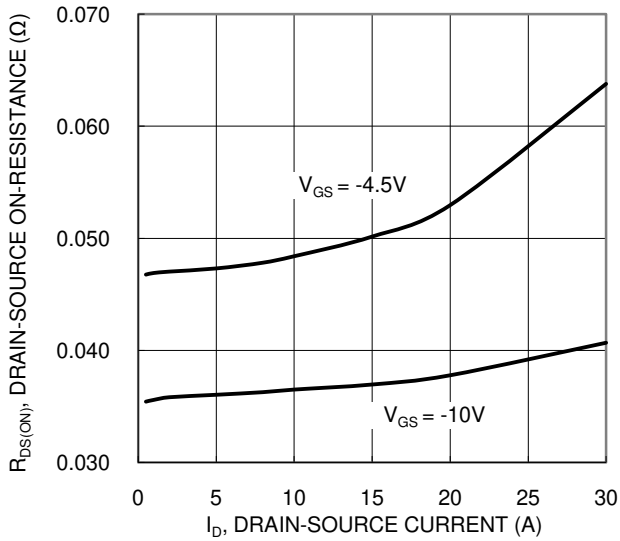


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

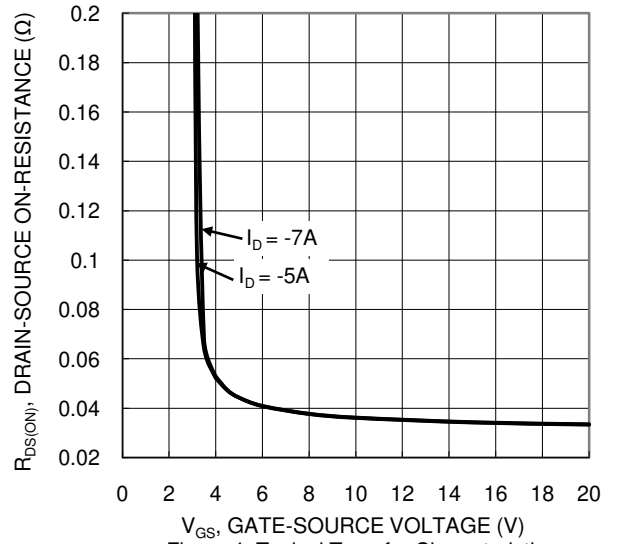


Figure 4. Typical Transfer Characteristic

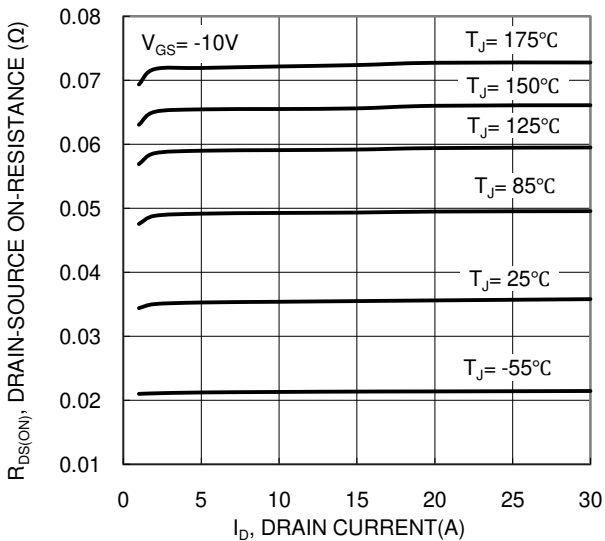


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

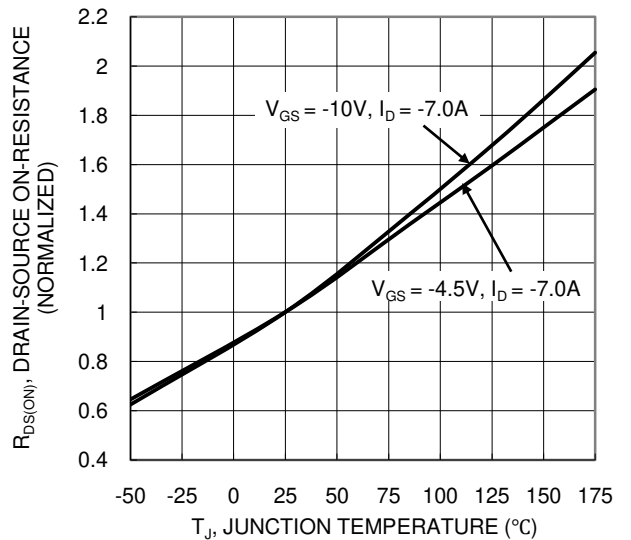
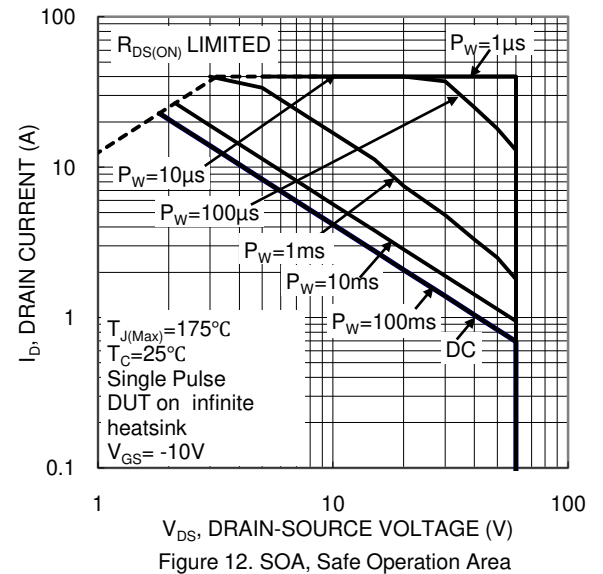
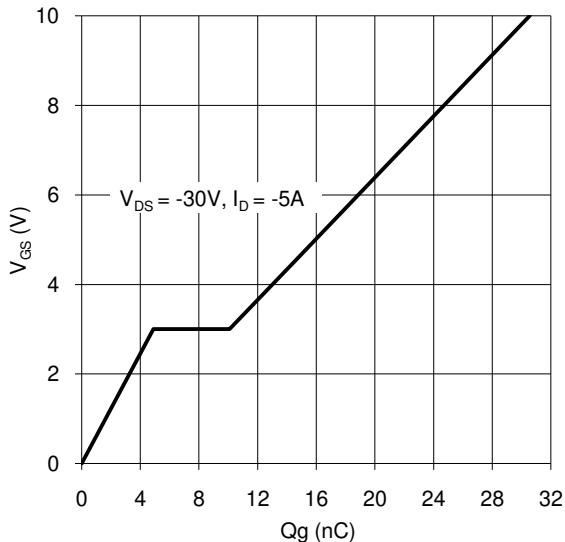
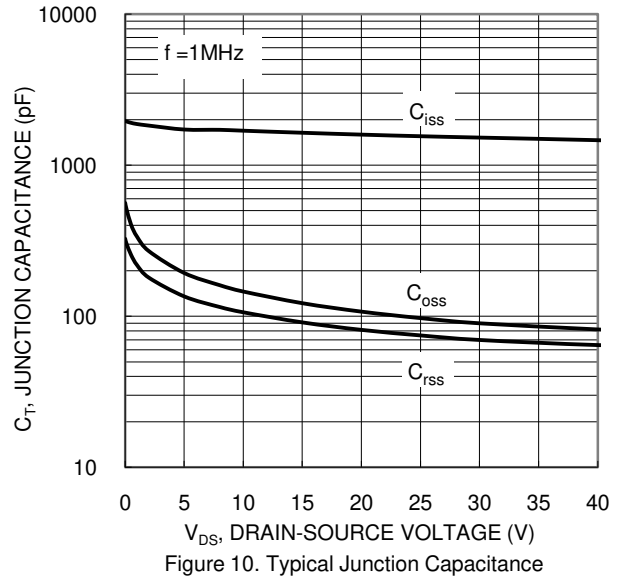
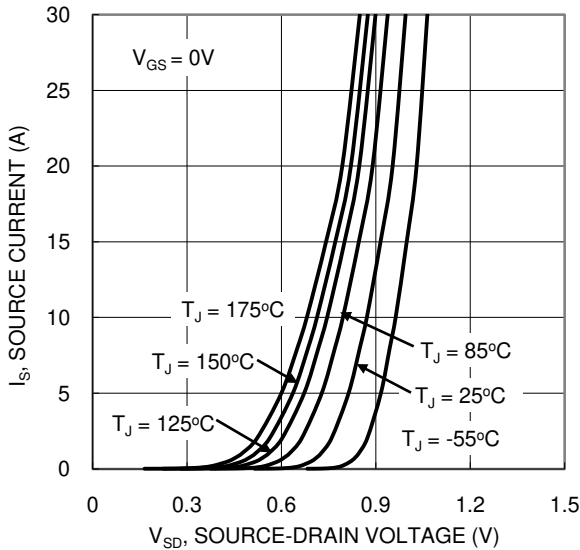
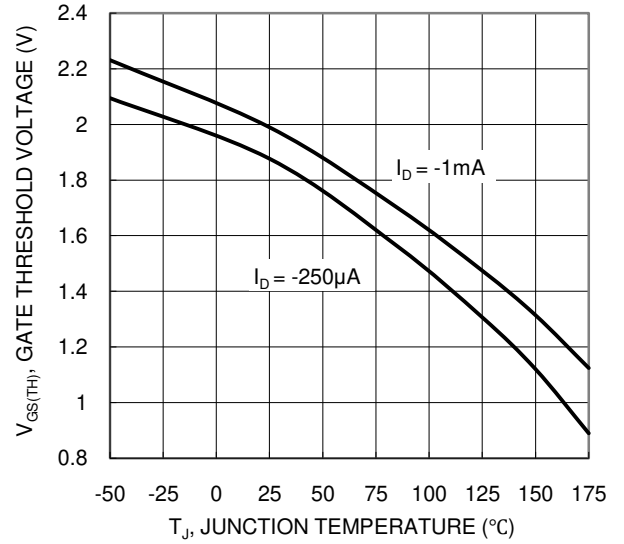
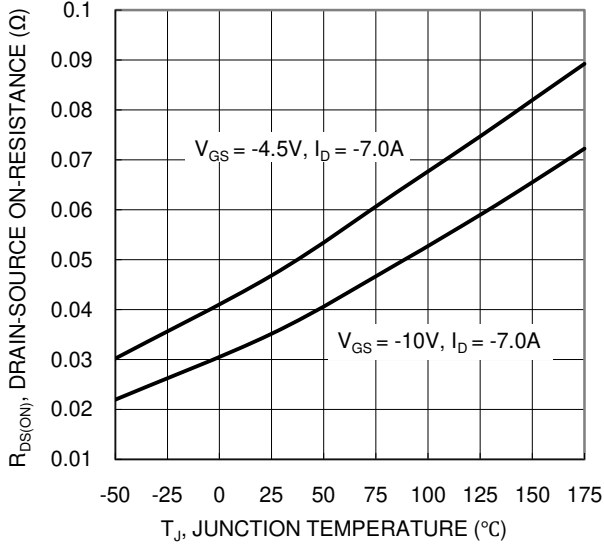


Figure 6. On-Resistance Variation with Temperature



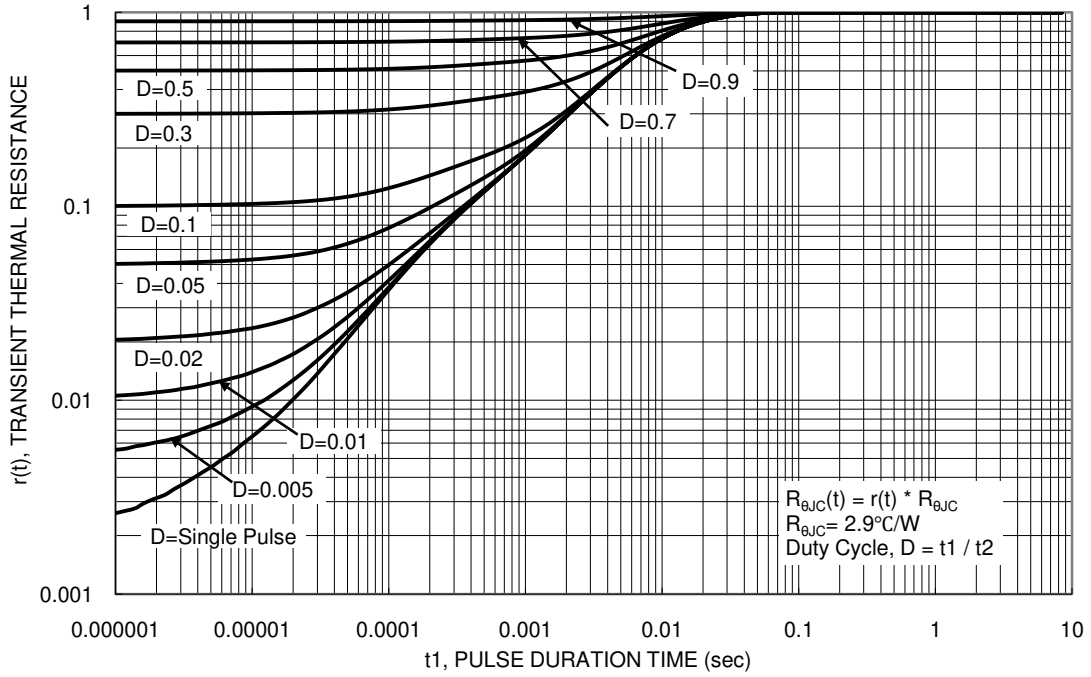
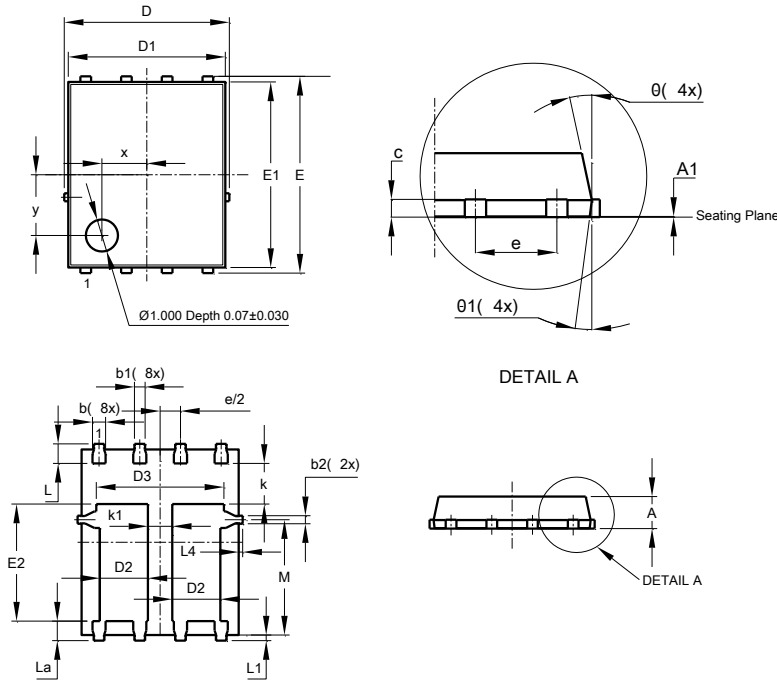


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8 (Type C)**

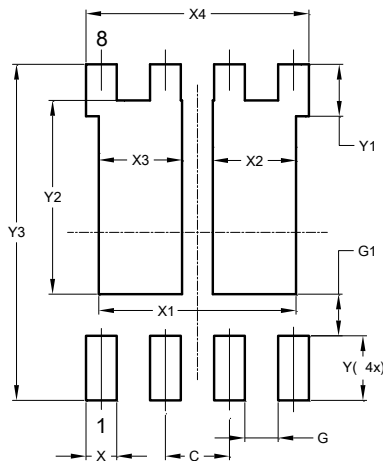


PowerDI5060-8 (Type C)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	1.40	1.60	1.50
D3	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.76	3.66
e	1.27BSC		
k	-	-	1.27
k1	0.56	-	-
L	0.51	0.71	0.61
La	0.51	0.71	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8 (Type C)**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	1.650
X3	1.650
X4	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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